2SC5809

Silicon NPN triple diffusion planar type

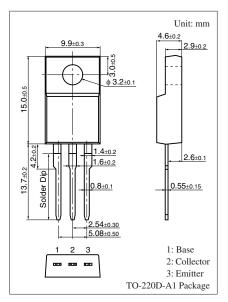
For high breakdown voltage high-speed switching

■ Features

- High-speed switching (Fall time t_f is short)
- ullet High collector-base voltage (Emitter open) V_{CBO}
- ullet Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- TO-220D built-in: Excellent package with withstand voltage 5 kV guaranteed

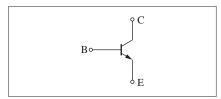
■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit		
Collector-base voltage (Emitter open)		V_{CBO}	800	V	
Collector-emitter voltage (Base open)		V _{CEO}	500	V	
Emitter-base voltage (Collector open)		V _{EBO}	8	V	
Collector current		I_C	3	A	
Peak collector current		I_{CP}	6	A	
Collector power	$T_C = 25^{\circ}C$	P _C	30	W	
dissipation	$T_a = 25^{\circ}C$		2		
Junction temperature		T_{j}	150	°C	
Storage temperature		T _{stg}	-55 to +150	°C	



Marking Symbol: C5809

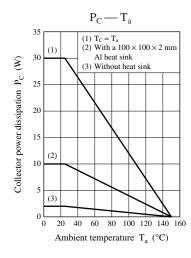
Internal Connection

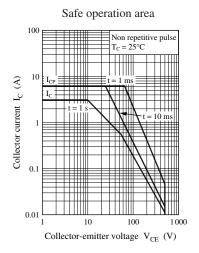


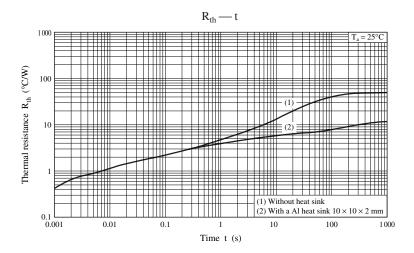
■ Electrical Characteristics $T_C = 25$ °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 10 \text{ mA}, I_B = 0$	500			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 800 \text{ V}, I_{E} = 0$			100	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 5 \text{ V}, I_{C} = 0$			100	μΑ
Forward current transfer ratio	h _{FE1}	$V_{CE} = 5 \text{ V}, I_{C} = 0.1 \text{ A}$	15			_
	h _{FE2}	$V_{CE} = 5 \text{ V}, I_{C} = 3 \text{ A}$	8			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 3 \text{ A}, I_B = 0.6 \text{ A}$		0.3	0.6	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_{C} = 0.5 \text{ A}, f = 1 \text{ MHz}$		8		MHz
Turn-on time	t _{on}	$I_C = 3.0 \text{ A}$, Resistance loaded		1.1		μs
Storage time	t _{stg}	$I_{B1} = 0.6 \text{ A}, I_{B2} = -0.6 \text{ A}$		2.0		μs
Fall time	$t_{\rm f}$	$V_{CC} = 200 \text{ V}$		0.3		μs

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.







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